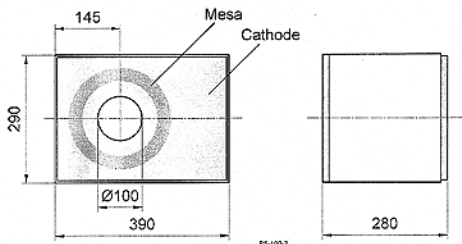


Preliminary data

Radiation	Type	Technology	Electrodes
Infrared	ELC-870-29-4	AlGaAs/GaAs	N (cathode) up

Outline (dimensions in microns)



Maximum Ratings

$T_{\text{amb}} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Forward current (DC)		I_F	50	mA
Peak forward current	$(t_p \leq 50 \mu\text{s}, t_p/T = 1/2)$	I_{FM}	100	mA

Optical and Electrical Characteristics

$T_{\text{amb}} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 20 \text{ mA}$	V_F		1.40		V
Forward voltage	$I_F = 50 \text{ mA}$	V_F		1.45		V
Reverse voltage	$I_R = 100 \mu\text{A}$	V_R	5			V
Radiant power	$I_F = 20 \text{ mA}$	Φ_e		0.7		mW
Radiant power	$I_F = 50 \text{ mA}$	Φ_e		1.7		mW
Radiant intensity	$I_F = 50 \text{ mA}$	I_e		0.7		mW/sr
Peak wavelength	$I_F = 50 \text{ mA}$	λ_p		879		nm
Spectral bandwidth at 50%	$I_F = 50 \text{ mA}$	$\Delta\lambda_{0.5}$		54		nm

Labeling

Type	Lot N°	Φ_e (typ, min, max)	Quantity
ELC-870-29-4			

Packing

Chips on adhesive film with wire-bond side on top